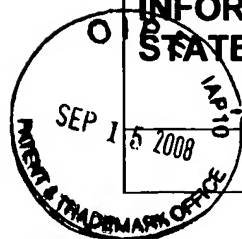


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First Named Inventor	Faris
Group Art Unit	1792
Examiner Name	Binh X. Tran
Attorney Docket Number	Reveo-0179

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First Named Inventor

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Examiner Name

Binh X. Tran

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	WO 99/05711A1	4-Feb-99	PCT				
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Examiner Signature		Date Considered	
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